

## P-Channel 60-V (D-S) MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
- 60	0.015 at $V_{GS} = - 10$ V	- 50 <sup>d</sup>
	0.020 at $V_{GS} = - 4.5$ V	- 50 <sup>d</sup>

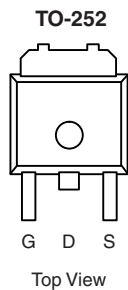
### FEATURES

- Halogen-free
- TrenchFET<sup>®</sup> Power MOSFET

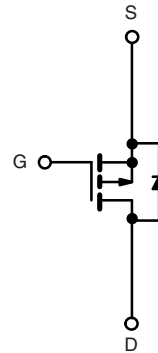

**RoHS**  
COMPLIANT

### APPLICATIONS

- Load Switch



Drain Connected to Tab


**Ordering Information:** SUD50P06-15-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	- 60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 175$ °C)	$I_D$	$T_C = 25$ °C	- 50 <sup>d</sup>
		$T_C = 125$ °C	- 27.5
Pulsed Drain Current	$I_{DM}$	- 80	A
Avalanche Current	$I_{AS}$	- 50	
Single Pulse Avalanche Energy <sup>a</sup>	L = 0.1 mH	$E_{AS}$	125
Power Dissipation	$P_D$	$T_C = 25$ °C	113 <sup>c</sup>
		$T_A = 25$ °C	2.5 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient <sup>b</sup>	$R_{thJA}$	$t \leq 10$ s	15	18
		Steady State	40	50
Junction-to-Case	$R_{thJC}$	0.82	1.1	°C/W

Notes:

- Duty cycle  $\leq 1$  %.
- When Mounted on 1" square PCB (FR-4 material).
- See SOA curve for voltage derating.
- Package limited.

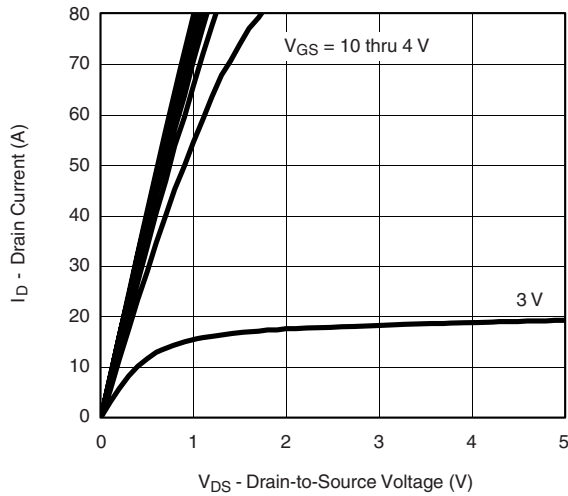
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 1		- 3	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$			- 1	$\mu\text{A}$
		$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			- 50	
		$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$			- 100	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	- 50			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -17\text{ A}$		0.012	0.015	$\Omega$
		$V_{GS} = -10\text{ V}, I_D = -50\text{ A}, T_J = 125\text{ }^\circ\text{C}$			0.025	
		$V_{GS} = -10\text{ V}, I_D = -50\text{ A}, T_J = 150\text{ }^\circ\text{C}$			0.028	
		$V_{GS} = -4.5\text{ V}, I_D = -14\text{ A}$			0.020	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -15\text{ V}, I_D = -17\text{ A}$		61		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1\text{ MHz}$		4950		$\text{pF}$
Output Capacitance	$C_{oss}$			480		
Reverse Transfer Capacitance	$C_{rss}$			405		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = -30\text{ V}, V_{GS} = -10\text{ V}, I_D = -50\text{ A}$		110	165	$\text{nC}$
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			19		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			28		
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = -30\text{ V}, R_L = 0.6\text{ }\Omega$ $I_D \cong -50\text{ A}, V_{GEN} = -10\text{ V}, R_G = 6\text{ }\Omega$		15	23	$\text{ns}$
Rise Time <sup>c</sup>	$t_r$			70	105	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			175	260	
Fall Time <sup>c</sup>	$t_f$			175	260	
<b>Source-Drain Diode Ratings and Characteristics</b> $T_C = 25\text{ }^\circ\text{C}^b$						
Continuous Current	$I_S$				- 50	A
Pulsed Current	$I_{SM}$				- 80	
Forward Voltage <sup>a</sup>	$V_{SD}$	$I_F = -50\text{ A}, V_{GS} = 0\text{ V}$		- 1.0	- 1.6	V
Reverse Recovery Time	$t_{rr}$	$I_F = -50\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$		45	70	ns

## Notes:

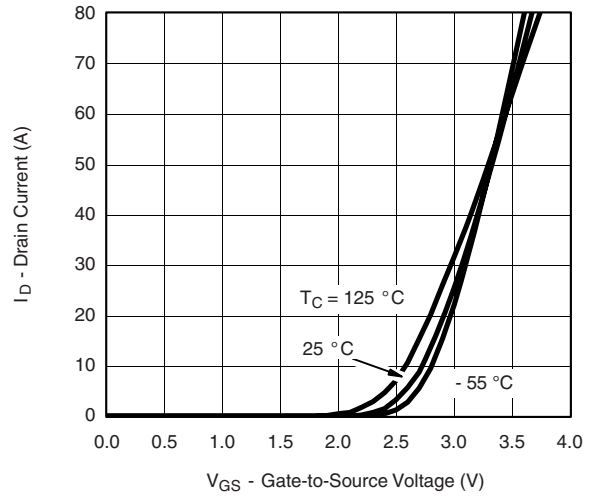
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.  
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

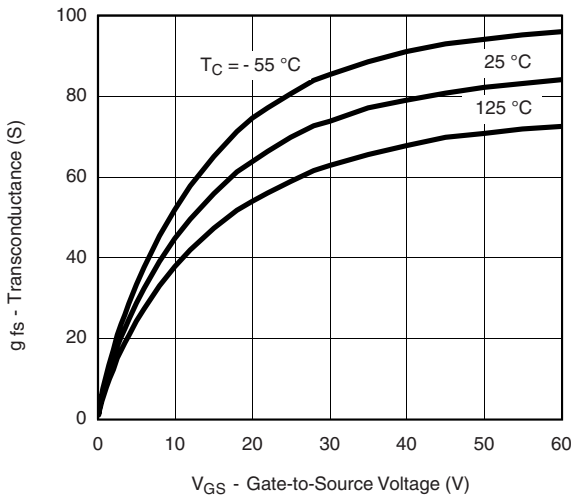
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



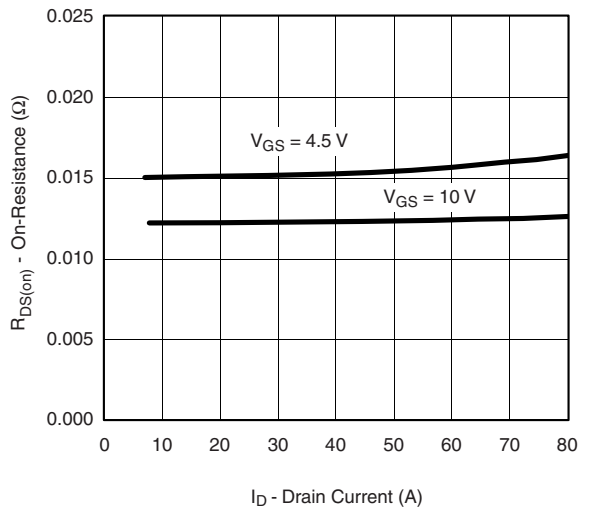
**Output Characteristics**



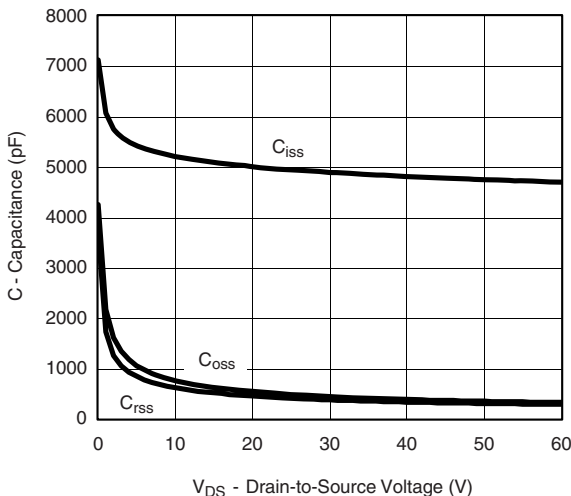
**Transfer Characteristics**



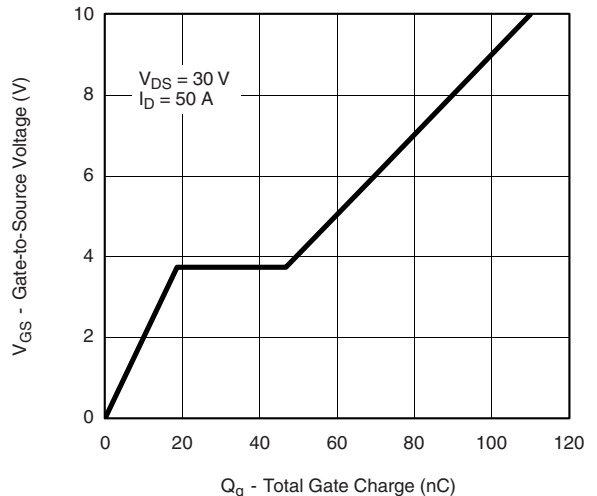
**Transconductance**



**On-Resistance vs. Drain Current**

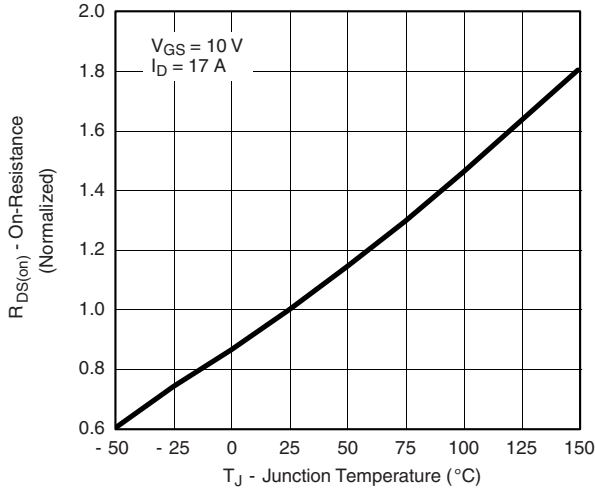


**Capacitance**

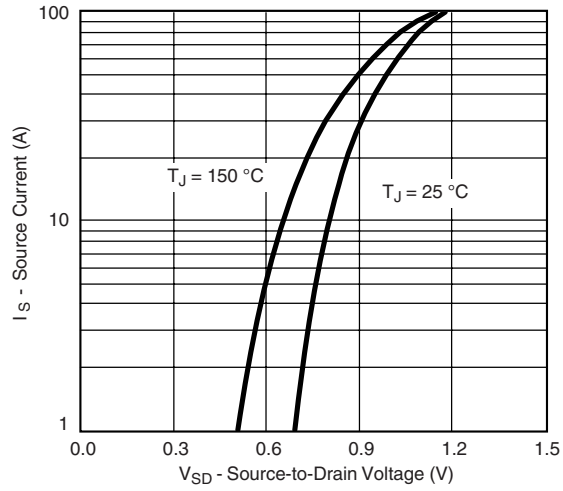


**Gate Charge**

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

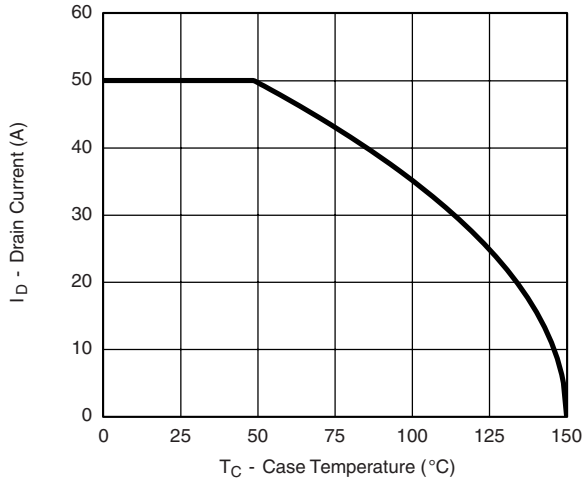


On-Resistance vs. Junction Temperature

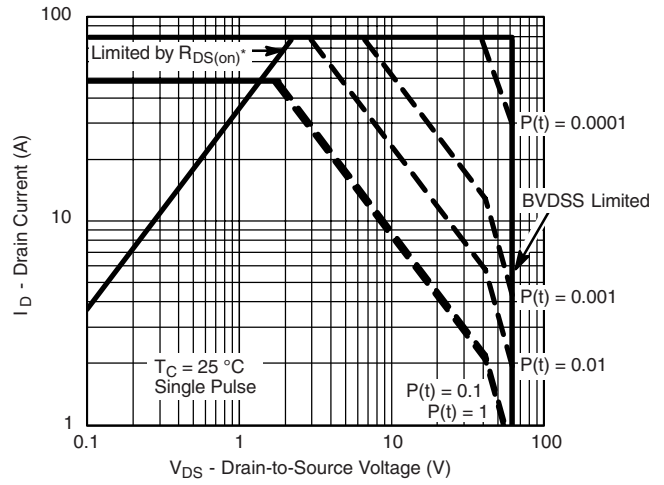


Source-Drain Diode Forward Voltage

### THERMAL RATINGS

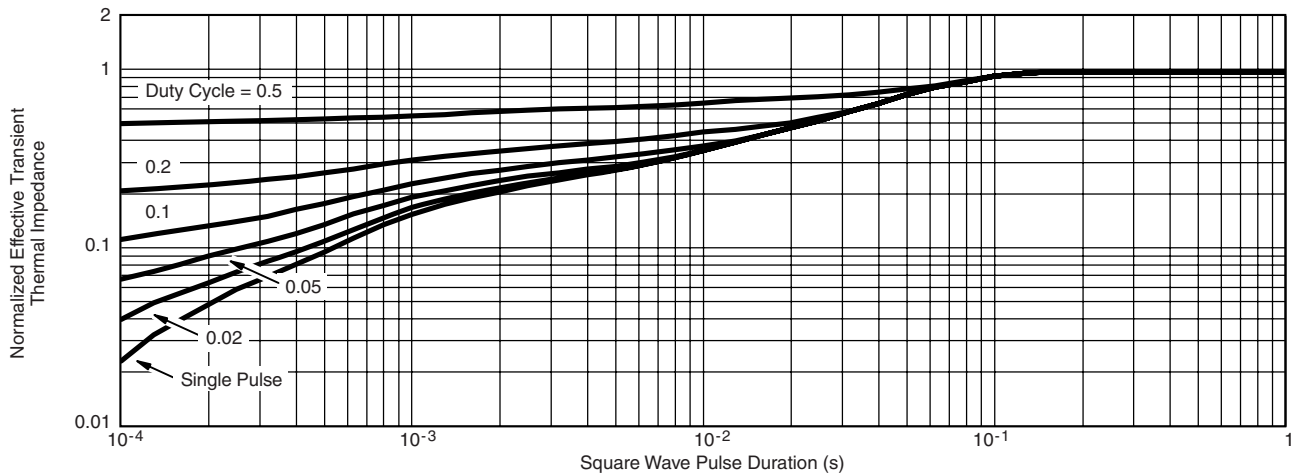


Drain Current vs. Case Temperature



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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